

## **SPECIFICATION AMENDMENTS:**

Please substitute the following amended paragraph for paragraph [0012]:

**[0012]** According to the abovementioned object, a transfective TFT-LCD panel and the manufacturing process thereof is provided in the present invention whose steps are disclosed below. First, form a first conductive layer on the substrate; next, define the first conductive layer to form a gate; after that, form a dielectric layer on the gate; following that, form a channel over the gate; then, form a photo-resist block; form a second conductive layer; next, define the second conductive to form a source and a drain over the gate, and to form a photo-reflective layer on the photo-resist block, wherein the photo-reflective layer and the drain are discrete; after that, form a protection layer thereon; following that, define the protection layer to form a first opening on the photo-reflective layer allowing part of the drain to be exposed, and to form a second opening on the photo-reflective layer allowing part of the photo-reflective layer to be exposed; last, form a transparent electrode, ~~and being electrically connected to the drain and the photo-reflective layer~~ are electrically connected via the transparent electrode through the first opening and the second opening respectively.

Please substitute the following amended paragraph for paragraph [0013]:

**[0013]** It is therefore another object of the invention to provide a transfective TFT-LCD panel. Equipped with both a transmissive area and a reflective area, the liquid crystal display panel further comprises a substrate, a thin film transistor, a dielectric layer, a photo-resist block, a photo-reflective layer, and a transparent electrode. The thin film transistor having a source, a drain and a gate is formed on the substrate; the dielectric layer is used to cover the gate; the photo-resist block is formed on the dielectric layer; the photo-reflective layer, which is located

within the reflective area ~~and is electrically connected to the drain~~, is formed on the photo-resist block, ~~wherein the photo-reflective layer and the drain are discrete~~; the transparent electrode, formed ~~substantially~~largely within the transmissive area, ~~The is electrically connected to the~~ photo-reflective layer is electrically connected to ~~and~~ the drain via the transparent electrode.

Please substitute the following amended paragraph for paragraph [0025]:

**[0025]** Please refer to FIG. 2F again. The transfective TFT-LCD panel formed through the manufacturing method according to the invention has a transmissive area R1 and a reflective area R2. The gate 202, the channel 208, the source 215 and the drain 220 together form a thin film transistor 240. The transparent electrode 235 is formed within the transmissive area R1 and is electrically connected to the drain 220. The photo-reflective layer 225, is located within the reflective area R2. It is noted that the photo-reflective layer 225 and the drain 220 are discrete (FIG. 2F), and the photo-reflective layer 225 is electrically connected to the drain 220 by the transparent electrode 235.

Please substitute the following amended paragraph for paragraph [0026]:

**[0026]** The feature of the invention resides in that the photo-reflective layer 225 within the reflective area R2 and the source 215 and the drain 220 of the thin film transistor, by means of a second metal layer, are formed simultaneously. Also, the photo-reflective layer 225 and the drain 220 are discrete, and the photo-reflective layer 225 is electrically connected to the drain 220 by the transparent electrode 235. Compared with the conventional manufacturing process which requires a third metal layer, the manufacturing process according to the present invention does not need to have the third metal layer hence reducing the number of masks needed.

Moreover, the manufacturing process according to the present invention is more simplified than that of the conventional one.